

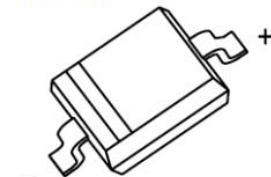
SOD-323 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管**■Features 特点**

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SOD-323

SOD-323**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B16WS	B110WS	Unit 单位
Device Marking 产品印字		B16	B110	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	60	100	V
DC Reverse Voltage 直流反向电压	V _R	60	100	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	42	70	V
Forward Rectified Current 正向整流电流	I _F	1		A
Peak Surge Current 峰值浪涌电流	I _{FSM}	25		A
Power Dissipation 耗散功率	P _D	300		mW
Thermal Resistance J-A 结到环境热阻	R _{θJA}	400		°C/W
Junction/Storage Temperature 结温/储藏温度	T _J , T _{stg}	-65 to +150 °C		°C

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B16WS	B110WS	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V _R	60	100	V	I _R =1mA
Forward Voltage 正向电压	V _F	0.7	0.85	V	I _F =1A
Reverse Current 反向电流	I _R	0.02(Ta=25°C) 5(Ta=100°C)		mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _T	30		pF	V _R =4V, f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

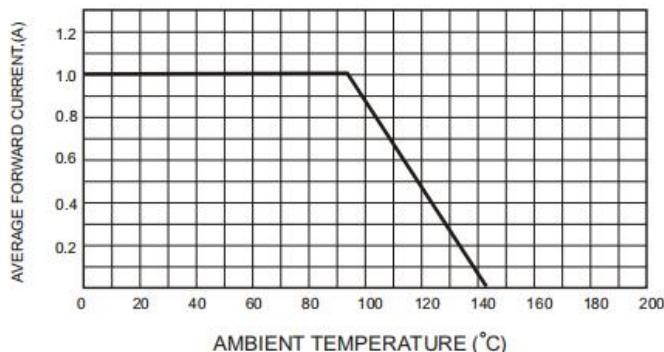


FIG.3 - Power Derating Curve

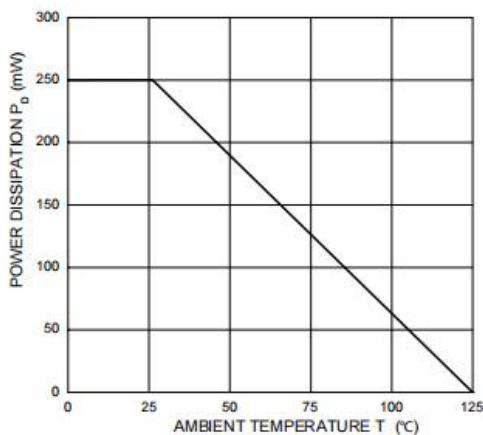


FIG.4-TYPICAL JUNCTION CAPACITANCE

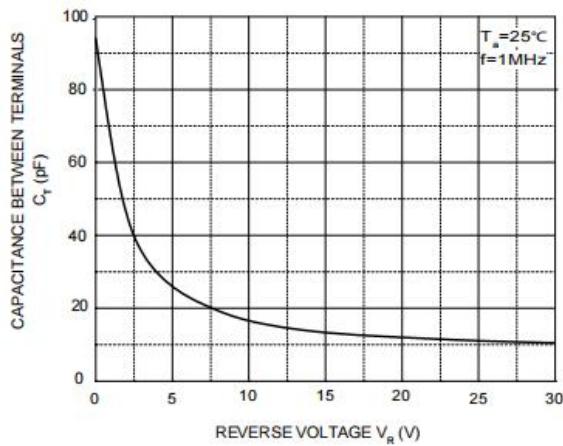


FIG.2-TYPICAL FORWARD

CHARACTERISTICS

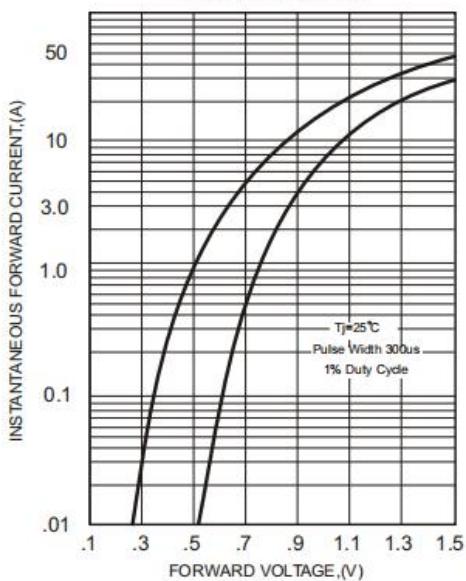
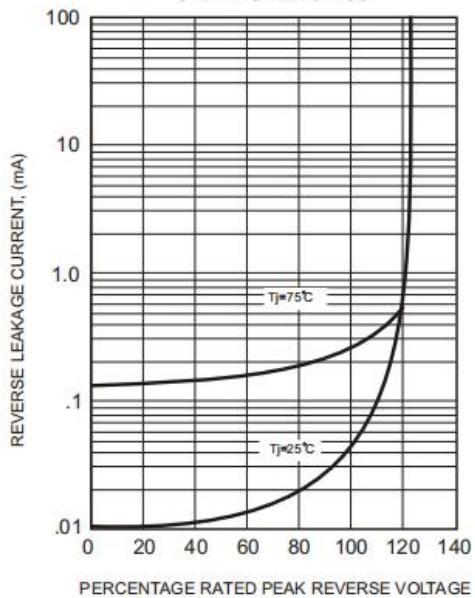


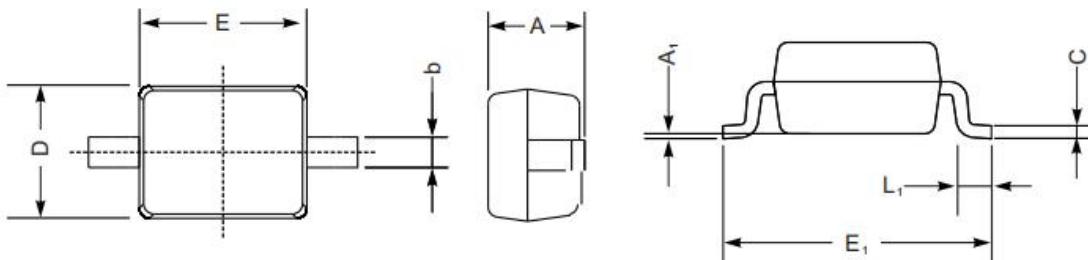
FIG.5 - TYPICAL REVERSE

CHARACTERISTICS



■ Dimension 外形封装尺寸

SOD323



UNIT		A	C	D	E	E_1	b	L_1	A_1
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—
mil	max	43	5.9	55	70	108	16	16	8
	min	32	3.1	47	63	100	9.8	7.9	—